

2SK2734

Silicon N Channel MOS FET
High Speed Power Switching

HITACHI

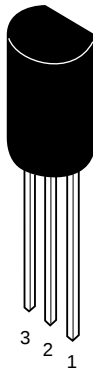
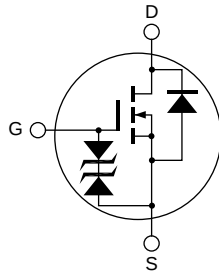
ADE-208-520
1st. Edition

Features

- Low on-resistance
 $R_{DS(on)} = 0.04\Omega$ typ (at $V_{GS} = 10\text{ V}$, $I_D = 2.5\text{ A}$)
- 4V gate drive devices.
- Large current capacitance
 $I_D = 5\text{ A}$

Outline

TO-92MOD.



1. Source
2. Drain
3. Gate

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	30	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	5	A
Drain peak current	I _{D(pulse)} ^{*1}	20	A
Body to drain diode reverse drain current	I _{DR}	5	A
Channel dissipation	Pch	0.9	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	−55 to +150	°C

Note: 1. PW ≤ 10μs, duty cycle ≤ 1 %

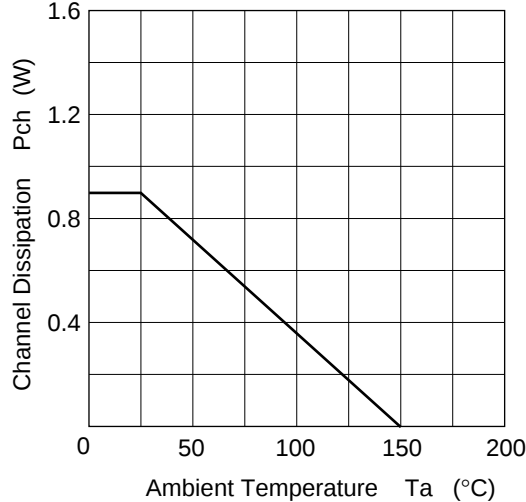
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	V _{(BR)DSS}	30	—	—	V	I _D = 10mA, V _{GS} = 0
Gate to source breakdown voltage	V _{(BR)GSS}	±20	—	—	V	I _G = ±100μA, V _{DS} = 0
Zero gate voltage drain current	I _{DSS}	—	—	10	μA	V _{DS} = 30 V, V _{GS} = 0
Gate to source leak current	I _{GSS}	—	—	±10	μA	V _{GS} = ±16V, V _{DS} = 0
Gate to source cutoff voltage	V _{GS(off)}	1.0	—	2.0	V	I _D = 1mA, V _{DS} = 10V
Static drain to source on state resistance	R _{DS(on)}	—	0.04	0.055	Ω	I _D = 2.5A, V _{GS} = 10V ^{*1}
	R _{DS(on)}	—	0.055	0.08	Ω	I _D = 2.5A, V _{GS} = 4V ^{*1}
Forward transfer admittance	y _{fs}	4	7	—	S	I _D = 2.5A, V _{DS} = 10V ^{*1}
Input capacitance	Ciss	—	550	—	pF	V _{DS} = 10V
Output capacitance	Coss	—	380	—	pF	V _{GS} = 0
Reverse transfer capacitance	Crss	—	155	—	pF	f = 1MHz
Turn-on delay time	t _{d(on)}	—	14	—	ns	V _{GS} = 10V, I _D = 2.5A
Rise time	t _r	—	80	—	ns	R _L = 4Ω
Turn-off delay time	t _{d(off)}	—	80	—	ns	
Fall time	t _f	—	65	—	ns	
Body to drain diode forward voltage	V _{DF}	—	1.0	—	V	I _F = 5A, V _{GS} = 0
Body to drain diode reverse recovery time	t _{rr}	—	40	—	ns	I _F = 5A, V _{GS} = 0 di _F / dt = 50A/μs

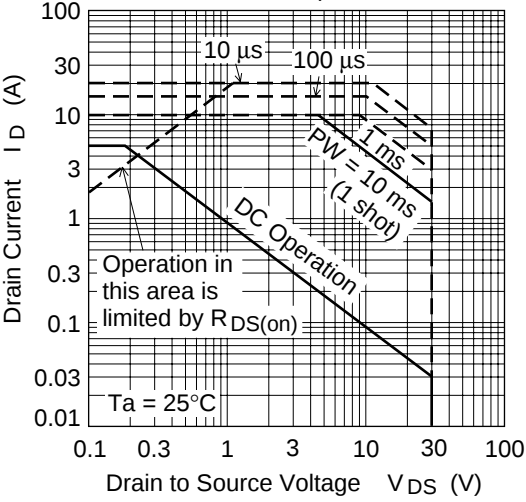
Note: 1. Pulse test

Main Characteristics

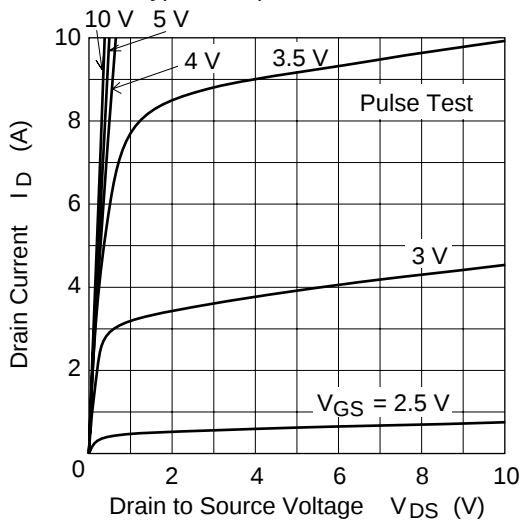
Power vs. Temperature Derating



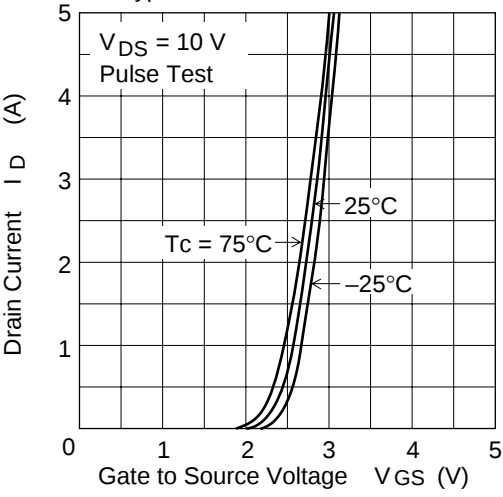
Maximum Safe Operation Area

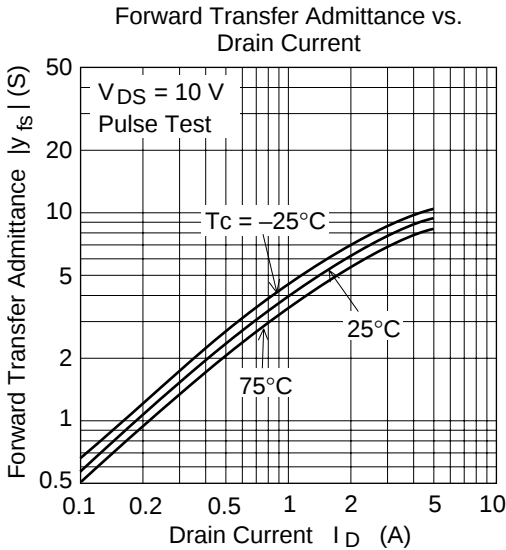
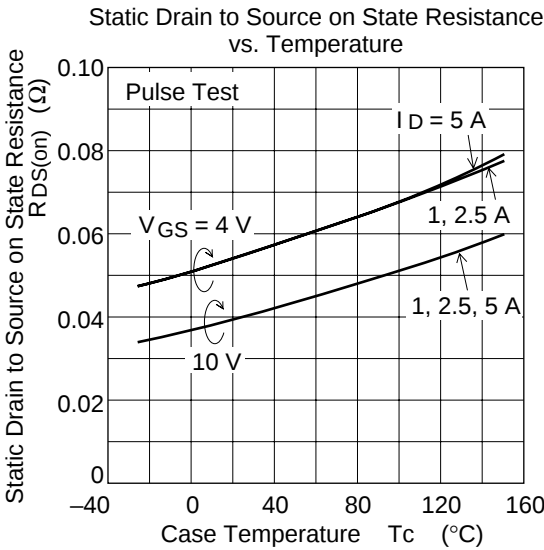
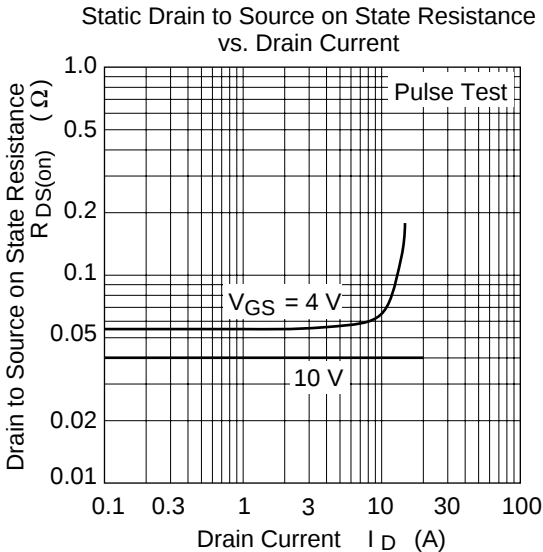
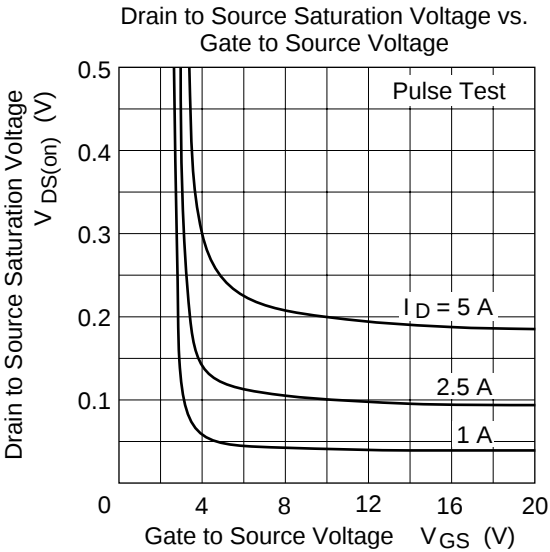


Typical Output Characteristics

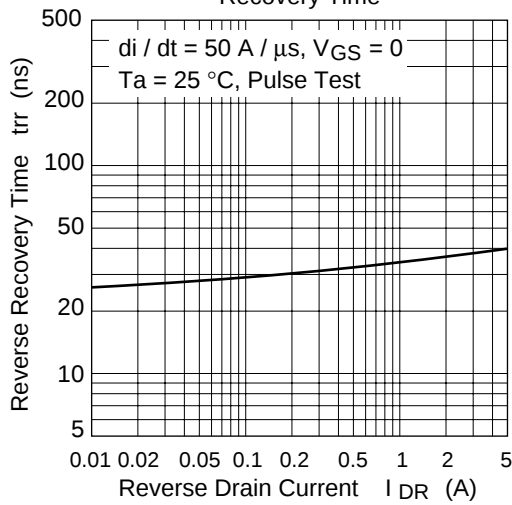


Typical Transfer Characteristics

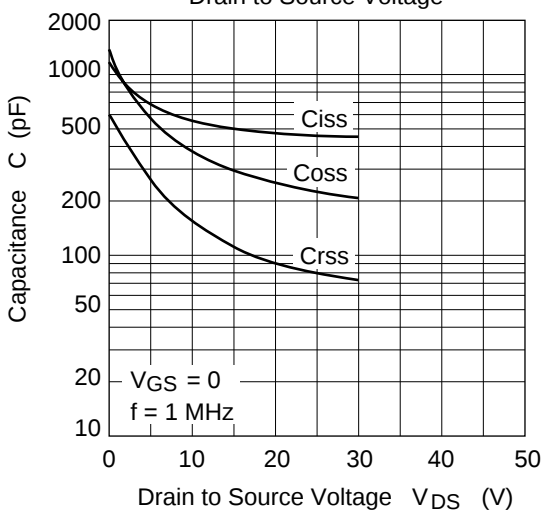




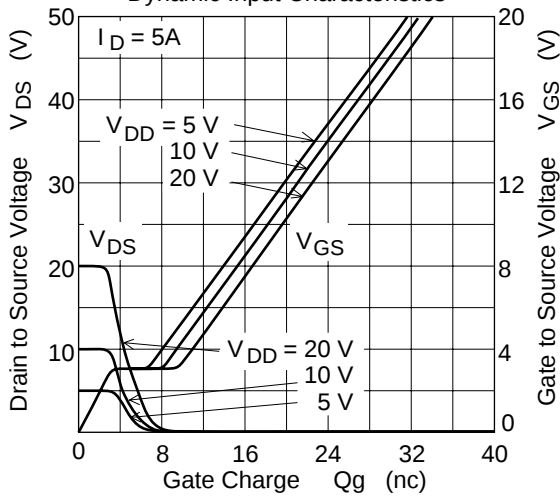
Body to Drain Diode Reverse Recovery Time



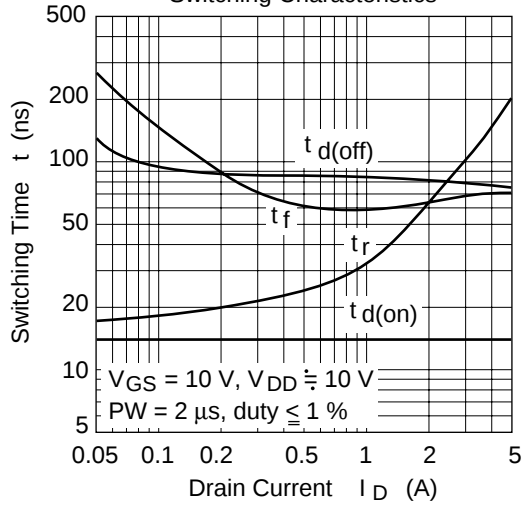
Typical Capacitance vs. Drain to Source Voltage

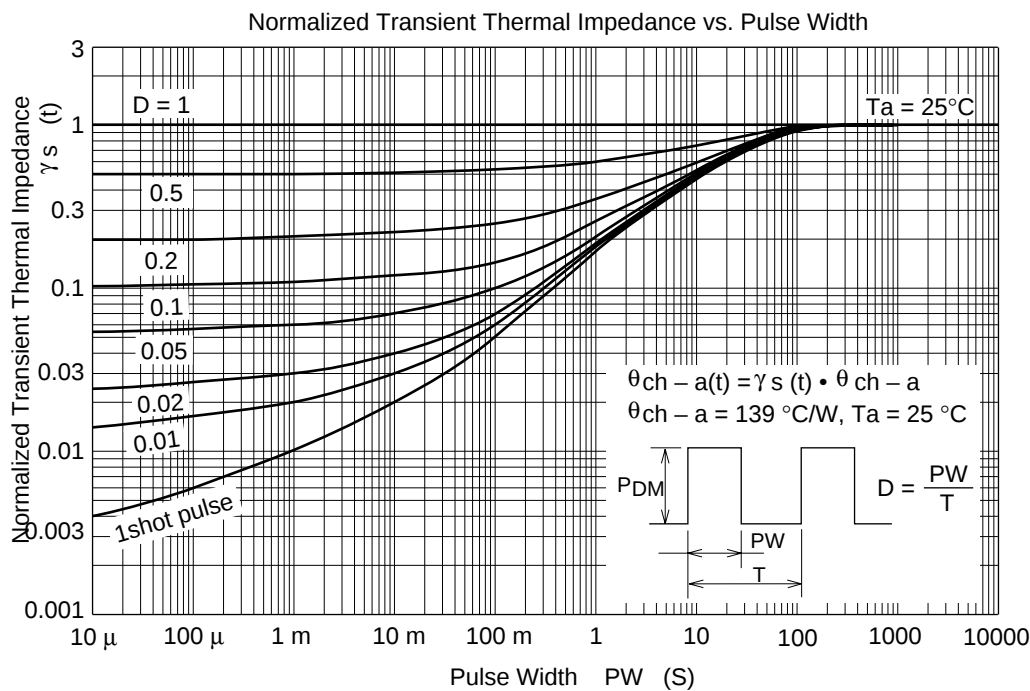
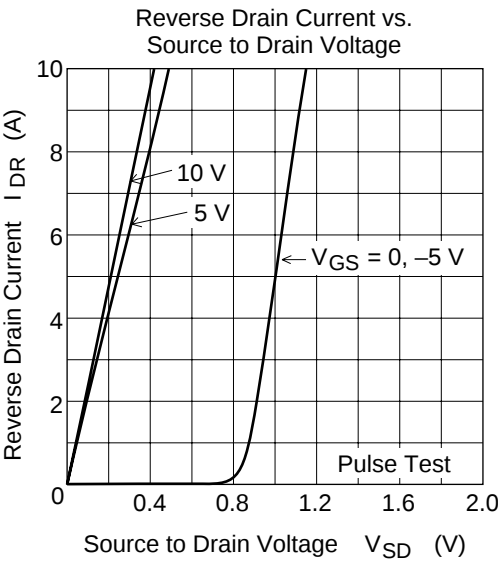


Dynamic Input Characteristics

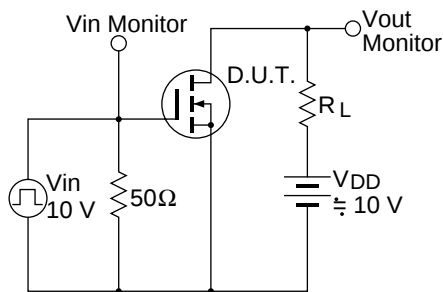


Switching Characteristics

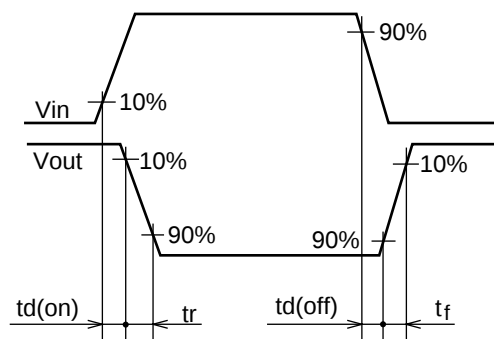




Switching Time Test Circuit

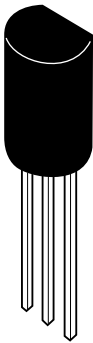
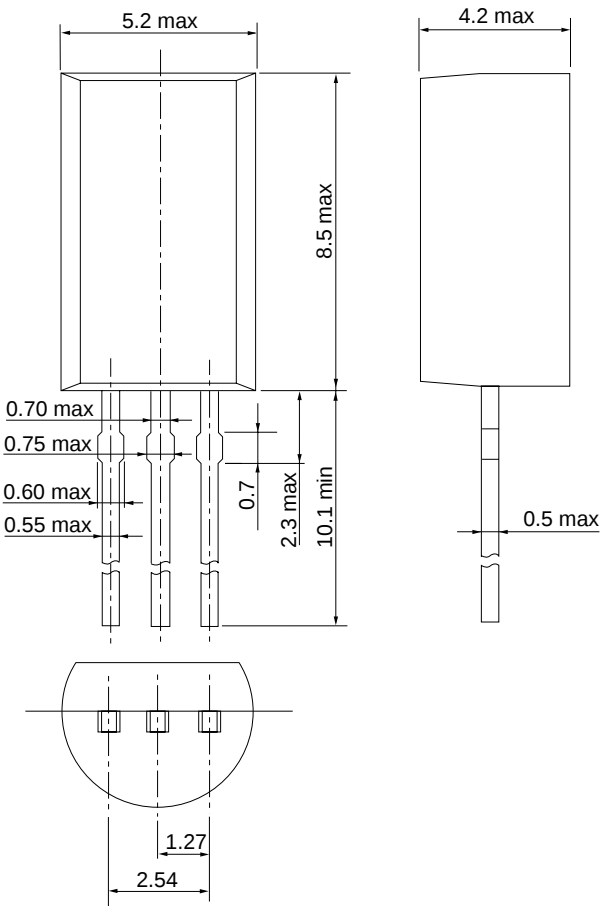


Switching Time Waveforms



Package Dimentions

Unit: mm



Hitachi Code	TO-92Mod.
EIAJ	SC-51
JEDEC	—

Cautions

1. Hitachi neither warrants nor grants licenses of any rights of Hitachi's or any third party's patent, copyright, trademark, or other intellectual property rights for information contained in this document. Hitachi bears no responsibility for problems that may arise with third party's rights, including intellectual property rights, in connection with use of the information contained in this document.
2. Products and product specifications may be subject to change without notice. Confirm that you have received the latest product standards or specifications before final design, purchase or use.
3. Hitachi makes every attempt to ensure that its products are of high quality and reliability. However, contact Hitachi's sales office before using the product in an application that demands especially high quality and reliability or where its failure or malfunction may directly threaten human life or cause risk of bodily injury, such as aerospace, aeronautics, nuclear power, combustion control, transportation, traffic, safety equipment or medical equipment for life support.
4. Design your application so that the product is used within the ranges guaranteed by Hitachi particularly for maximum rating, operating supply voltage range, heat radiation characteristics, installation conditions and other characteristics. Hitachi bears no responsibility for failure or damage when used beyond the guaranteed ranges. Even within the guaranteed ranges, consider normally foreseeable failure rates or failure modes in semiconductor devices and employ systemic measures such as fail-safes, so that the equipment incorporating Hitachi product does not cause bodily injury, fire or other consequential damage due to operation of the Hitachi product.
5. This product is not designed to be radiation resistant.
6. No one is permitted to reproduce or duplicate, in any form, the whole or part of this document without written approval from Hitachi.
7. Contact Hitachi's sales office for any questions regarding this document or Hitachi semiconductor products.

HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL	NorthAmerica	:	http://semiconductor.hitachi.com/
	Europe	:	http://www.hitachi-eu.com/hel/ecg
	Asia (Singapore)	:	http://www.has.hitachi.com.sg/grp3/sicd/index.htm
	Asia (Taiwan)	:	http://www.hitachi.com.tw/E/Product/SICD_Frame.htm
	Asia (HongKong)	:	http://www.hitachi.com.hk/eng/bo/grp3/index.htm
	Japan	:	http://www.hitachi.co.jp/Sicd/indx.htm

For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive, San Jose, CA 95134 Tel: <1> (408) 433-1990 Fax: <1> (408) 433-0223	Hitachi Europe GmbH Electronic components Group Dornacher Straße 3 D-85622 Feldkirchen, Munich Germany Tel: <49> (89) 9 9180-0 Fax: <49> (89) 9 29 30 00 Hitachi Europe Ltd. Electronic Components Group. Whitebrook Park Lower Cookham Road Maidenhead Berkshire SL6 8YA, United Kingdom Tel: <44> (1628) 585000 Fax: <44> (1628) 778322
--	---

Hitachi Asia Pte. Ltd. 16 Collyer Quay #20-00 Hitachi Tower Singapore 049318 Tel: 535-2100 Fax: 535-1533 Hitachi Asia Ltd. Taipei Branch Office 3F, Hung Kuo Building, No.167, Tun-Hwa North Road, Taipei (105) Tel: <886> (2) 2718-3666 Fax: <886> (2) 2718-8180
--

Hitachi Asia (Hong Kong) Ltd. Group III (Electronic Components) 7/F., North Tower, World Finance Centre, Harbour City, Canton Road, Tsim Sha Tsui, Kowloon, Hong Kong Tel: <852> (2) 735 9218 Fax: <852> (2) 730 0281 Telex: 40815 HITEC HX
--

Copyright ' Hitachi, Ltd., 1999. All rights reserved. Printed in Japan.